## **SQ2309ES**

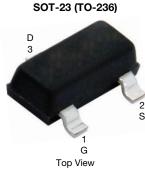
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D

## Automotive P-Channel 60 V (D-S) 175 °C MOSFET



#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified <sup>c</sup>
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

G

P-Channel MOSFET

(for detailed order number please see www.vishay.com/doc?79771)



COMPLIANT HALOGEN

Marking code: 8P

| PRODUCT SUMMARY                                     |        |  |  |  |
|---|--------|--|--|--|
| V <sub>DS</sub> (V)                                 | -60    |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -10 V  | 0.335  |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -4.5 V | 0.500  |  |  |  |
| I <sub>D</sub> (A)                                  | -1.7   |  |  |  |
| Configuration                                       | Single |  |  |  |

# ORDERING INFORMATION Package SOT-23 Lead (Pb)-free and halogen-free SQ2309ES (for detailed order number places are unusiden as an unit of the second secon

| PARAMETER                                    |                         | SYMBOL                            | LIMIT       | UNIT |
|--|-------------------------|-----------------------------------|-------------|------|
| Drain-source voltage                         |                         | V <sub>DS</sub>                   | -60         | V    |
| Gate-source voltage                          |                         | V <sub>GS</sub>                   | ± 20        |      |
| Continuous drain surrant                     | T <sub>C</sub> = 25 °C  | I                                 | -1.7        |      |
| Continuous drain current                     | T <sub>C</sub> = 125 °C | I <sub>D</sub>                    | -1          |      |
| Continuous source current (diode conduction) |                         | IS                                | -2.6        | А    |
| Pulsed drain current <sup>a</sup>            |                         | I <sub>DM</sub>                   | -6.8        |      |
| Single pulse avalanche current               | L = 0.1 mH              | I <sub>AS</sub>                   | -6.8        |      |
| Single pulse avalanche energy                | L = 0.1 MH              | E <sub>AS</sub>                   | 2.3         | mJ   |
| Maximum power dissipation <sup>a</sup>       | T <sub>C</sub> = 25 °C  | D                                 | 2           | w    |
|  | T <sub>C</sub> = 125 °C | PD                                | 0.6         | ~~   |
| Operating junction and storage temperature   | range                   | T <sub>J</sub> , T <sub>stq</sub> | -55 to +175 | °C   |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |  |  |
|----------------------------|------------------------|-------------------|-------|------|--|--|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |  |  |
| Junction-to-ambient        | PCB mount <sup>b</sup> | R <sub>thJA</sub> | 166   | °C/W |  |  |
| Junction-to-foot (drain)   |                        | R <sub>thJF</sub> | 73    | 0/11 |  |  |

#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing

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SQ2309ES

| <b>\</b> /' | 0.1      |      |      |
|-------------|----------|------|------|
| Vichov      | <u> </u> | INAR |      |
| Vishay      | OII      | IUUI | 11 7 |
|             |          |      |      |

| PARAMETER                                     | SYMBOL                    | TEST CONDITIONS  |  | MIN. | TYP.  | MAX.  | UNIT |  |
|---|---------------------------|--|--|------|-------|-------|------|--|
| Static  |                           |  |  |      |       |       |      |  |
| Drain-source breakdown voltage                | V <sub>DS</sub>           | V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA  |  | -60  | -     | -     |      |  |
| Gate-source threshold voltage                 | V <sub>GS(th)</sub>       | V <sub>DS</sub> =  | V <sub>GS</sub> , I <sub>D</sub> = -250 μA             | -1.5 | -2.0  | -2.5  | V    |  |
| Gate-source leakage                           | I <sub>GSS</sub>          | V <sub>DS</sub> =  | $V_{DS} = 0 V, V_{GS} = \pm 20 V$                      |      | -     | ± 100 | nA   |  |
|   |                           | $V_{GS} = 0 V$   | V <sub>DS</sub> = -60 V                                | -    | -     | -1    | 1    |  |
| Zero gate voltage drain current               | I <sub>DSS</sub>          | $V_{GS} = 0 V$   | V <sub>DS</sub> = -60 V, T <sub>J</sub> = 125 °C       | -    | -     | -50   | μA   |  |
|   |                           | V <sub>GS</sub> = 0 V  | V <sub>DS</sub> = -60 V, T <sub>J</sub> = 175 °C       | -    | -     | -150  |      |  |
| On-state drain current <sup>a</sup>           | I <sub>D(on)</sub>        | V <sub>GS</sub> = -10 V  | $V_{DS} \le -5 V$                                      | -5   | -     | -     | Α    |  |
| Drain-source on-state resistance <sup>a</sup> |                           | V <sub>GS</sub> = -10 V  | I <sub>D</sub> = -1.25 A                               | -    | 0.268 | 0.335 | Ω    |  |
|   |                           | V <sub>GS</sub> = -10 V  | I <sub>D</sub> = -1.25 A, T <sub>J</sub> = 125 °C      | -    | -     | 0.567 |      |  |
|   | R <sub>DS(on)</sub>       | V <sub>GS</sub> = -10 V  | I <sub>D</sub> = -1.25 A, T <sub>J</sub> = 175 °C      | -    | -     | 0.704 |      |  |
|   |                           | V <sub>GS</sub> = -4.5 V   | I <sub>D</sub> = -1 A                                  | -    | 0.370 | 0.500 |      |  |
| Forward transconductance b                    | g <sub>fs</sub>           |  | = -5 V, I <sub>D</sub> = -1 A                          | -    | 1.8   | -     | S    |  |
| Dynamic <sup>b</sup>                          | 0.0                       |  |  |      | I.    | I.    | 1    |  |
| Input capacitance                             | C <sub>iss</sub>          |  |  |      | 211   | 265   | 1    |  |
| Output capacitance                            | C <sub>oss</sub>          | $V_{GS} = 0 V$   | V <sub>DS</sub> = -25 V, f = 1 MHz                     | -    | 30    | 40    | pF   |  |
| Reverse transfer capacitance                  | C <sub>rss</sub>          |  |  | -    | 21    | 30    |      |  |
| Total gate charge <sup>c</sup>                | Qg                        |  |  | -    | 5.5   | 8.5   |      |  |
| Gate-source charge <sup>c</sup>               | Q <sub>gs</sub>           | V <sub>GS</sub> = -10 V  | $V_{DS} = -30 \text{ V}, \text{ I}_{D} = -1 \text{ A}$ | -    | 0.8   | -     | nC   |  |
| Gate-drain charge <sup>c</sup>                | Q <sub>gd</sub>           |  |  | -    | 1.3   | -     |      |  |
| Gate resistance                               | Rg                        | f = 1 MHz  |  | 4.95 | 9.88  | 14.80 | Ω    |  |
| Turn-on delay time <sup>c</sup>               | t <sub>d(on)</sub>        |  |  | -    | 5     | 8     |      |  |
| Rise time <sup>c</sup>                        | tr                        | $\label{eq:VDD} \begin{array}{l} V_{DD}=\text{-30 V},R_{L}=\text{30 }\Omega\\ I_{D}\cong\text{-3 A},V_{GEN}=\text{-10 V},R_{g}=\text{1}\ \Omega \end{array}$ |  | -    | 9     | 14    | - ns |  |
| Turn-off delay time <sup>c</sup>              | t <sub>d(off)</sub>       |  |  | -    | 12    | 18    |      |  |
| Fall time <sup>c</sup>                        | t <sub>f</sub>            |  |  | -    | 9     | 14    |      |  |
| Source-Drain Diode Ratings and Cha            | racteristics <sup>b</sup> |  |  |      |       |       |      |  |
| Pulsed current <sup>a</sup>                   | I <sub>SM</sub>           |  |  | -    | -     | -6.8  | А    |  |
| Forward voltage                               | V <sub>SD</sub>           | I <sub>F</sub> =   | -1.5 A, V <sub>GS</sub> = 0 V                          | -    | -0.85 | -1.2  | V    |  |

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

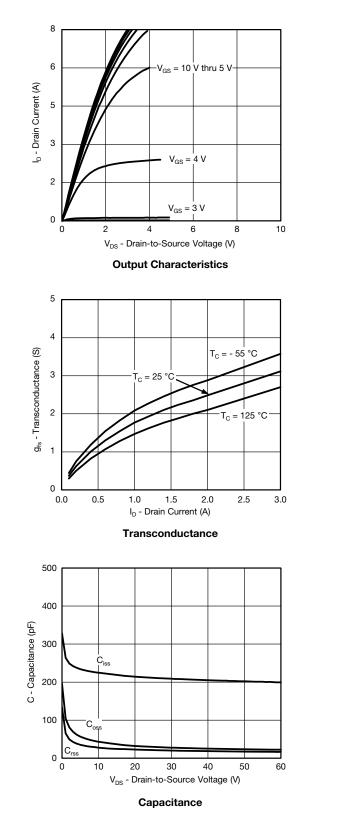
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

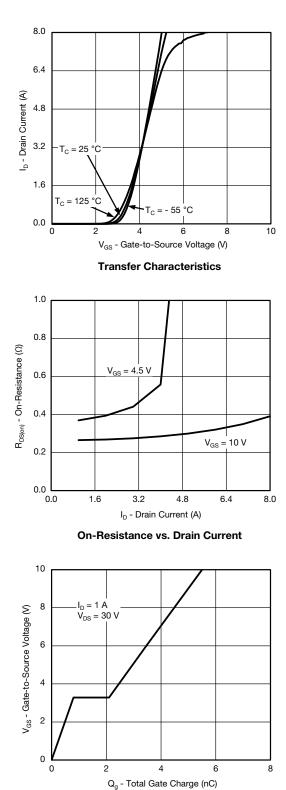
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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





Gate Charge

S21-1074-Rev. C, 15-Nov-2021

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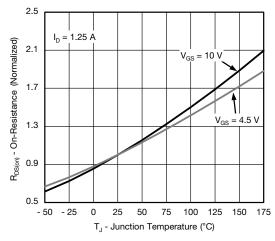
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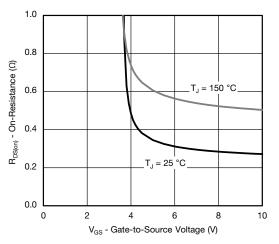
## **SQ2309ES**

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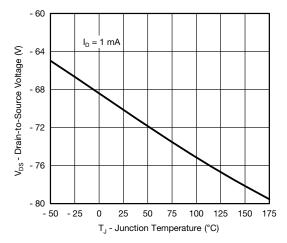
#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



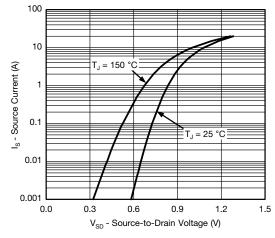
**On-Resistance vs. Junction Temperature** 



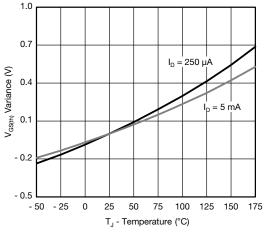
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage





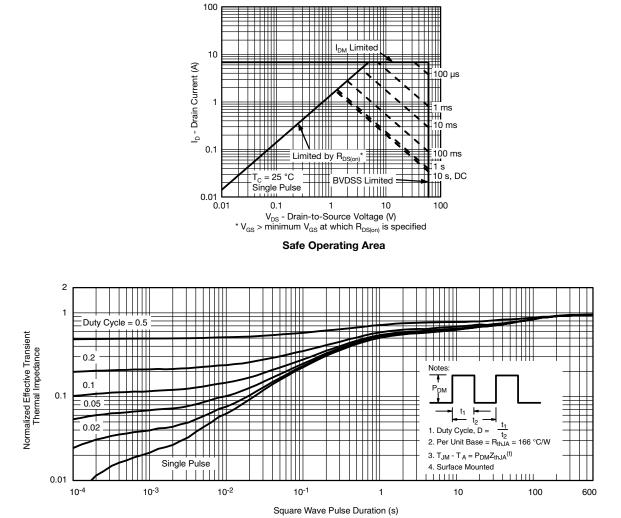
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



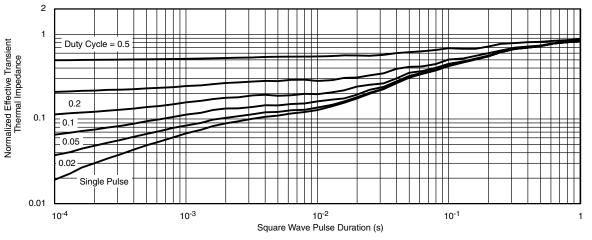
Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

S21-1074-Rev. C, 15-Nov-2021

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# Package Information

Vishay Siliconix

#### SOT-23 (TO-236): 3-LEAD







| Dim            | MILLIN   | METERS   | INCHES     |            |  |  |
|----------------|----------|----------|------------|------------|--|--|
|                | Min      | Max      | Min        | Мах        |  |  |
| Α              | 0.89     | 1.12     | 0.035      | 0.044      |  |  |
| A <sub>1</sub> | 0.01     | 0.10     | 0.0004     | 0.004      |  |  |
| A <sub>2</sub> | 0.88     | 1.02     | 0.0346     | 0.040      |  |  |
| b              | 0.35     | 0.50     | 0.014      | 0.020      |  |  |
| С              | 0.085    | 0.18     | 0.003      | 0.007      |  |  |
| D              | 2.80     | 3.04     | 0.110      | 0.120      |  |  |
| E              | 2.10     | 2.64     | 0.083      | 0.104      |  |  |
| E <sub>1</sub> | 1.20     | 1.40     | 0.047      | 0.055      |  |  |
| е              | 0.95     | 0.95 BSC |            | 0.0374 Ref |  |  |
| e <sub>1</sub> | 1.90 BSC |          | 0.0748 Ref |            |  |  |
| L              | 0.40     | 0.60     | 0.016      | 0.024      |  |  |
| L <sub>1</sub> | 0.6      | 0.64 Ref |            | 5 Ref      |  |  |
| S              | 0.50 Ref |          | 0.020 Ref  |            |  |  |
| q              | 3°       | 8°       | 3°         | 8°         |  |  |



# Application Note 826

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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